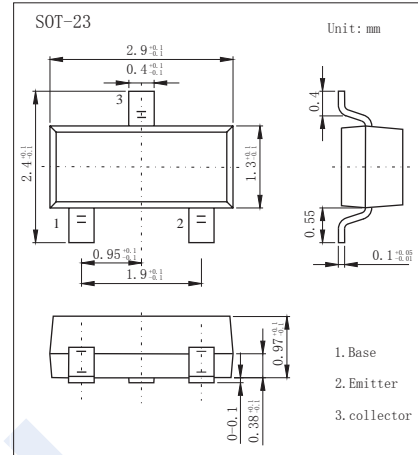


## PNP Transistors

## 2KA2010

## ■ Features

- High voltage transistor
- Low collector-emitter saturation voltage
- Complementary to 2KC2010 (NPN)

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	-300	V
Collector - Emitter Voltage	$V_{CE0}$	-300	
Emitter - Base Voltage	$V_{EB0}$	-5	
Collector Current - Continuous	$I_C$	-500	mA
Collector Power Dissipation	$P_C$	350	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CB0}$	$I_C = -100 \mu\text{A}$ , $I_E = 0$	-300			V
Collector- emitter breakdown voltage	$V_{CE0}$	$I_C = -1 \text{mA}$ , $I_B = 0$	-300			
Emitter - base breakdown voltage	$V_{EB0}$	$I_E = -100 \mu\text{A}$ , $I_C = 0$	-5			
Collector-base cut-off current	$I_{CB0}$	$V_{CB} = -200 \text{V}$ , $I_E = 0$			-0.25	$\mu\text{A}$
Emitter cut-off current	$I_{EB0}$	$V_{EB} = -5 \text{V}$ , $I_C = 0$			-0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -20 \text{mA}$ , $I_B = -2 \text{mA}$			-0.2	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = -20 \text{mA}$ , $I_B = -2 \text{mA}$			-0.9	
DC current gain	$h_{fe} (1)$	$V_{CE} = -10 \text{V}$ , $I_C = -1 \text{mA}$	60			
	$h_{fe} (2)$	$V_{CE} = -10 \text{V}$ , $I_C = -10 \text{mA}$	100		300	
	$h_{fe} (3)$	$V_{CE} = -10 \text{V}$ , $I_C = -30 \text{mA}$	60			
Transition frequency	$f_T$	$V_{CE} = -20 \text{V}$ , $I_C = -10 \text{mA}$ , $f = 30 \text{MHz}$	50			MHz

## ■ Marking

Marking	4C
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### Typical Characteristics

